Voltage Regulators, Peak Power Zener Surge Rated, 600 Watt

BZG03C15 Series

The SMA series is supplied in ON Semiconductor's exclusive, cost-effective, highly reliable SURMETIC™ package and is ideally suited for use in communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications. This new line of 1.5 watt Zener diodes offers the following advantages:

Specification Features

- Standard Zener Breakdown Voltage – 15 V to 150 V
- Peak Power 600 Watts @ 100 μs
- ESD Rating of Class 3 (> 16 KV) per Human Body Model
- Response Time is Typically < 1.0 ns
- Flat Handling Surface for Accurate Placement
- Package Design for Top Slide or Bottom Circuit Board Mounting
- Low Profile Package
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

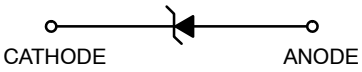
Mechanical Characteristics

CASE: Void-free, transfer-molded plastic
FINISH: All external surfaces are corrosion resistant and leads are readily solderable
MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES: 260°C for 10 Seconds
POLARITY: Cathode indicated by molded polarity notch or polarity band
MOUNTING POSITION: Any

ON Semiconductor®

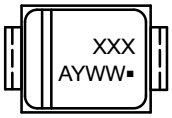
www.onsemi.com

PLASTIC SURFACE MOUNT ZENER VOLTAGE REGULATORS 600 WATTS PEAK POWER



SMA
CASE 403D

MARKING DIAGRAM



XXX	= Specific Device Code (See Table on Page 2)
A	= Assembly Location
Y	= Year
WW	= Work Week
▪	= Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
BZG03C15G	SMA (Pb−Free)	5000/Tape & Reel
BZG03C150G	SMA (Pb−Free)	5000/Tape & Reel

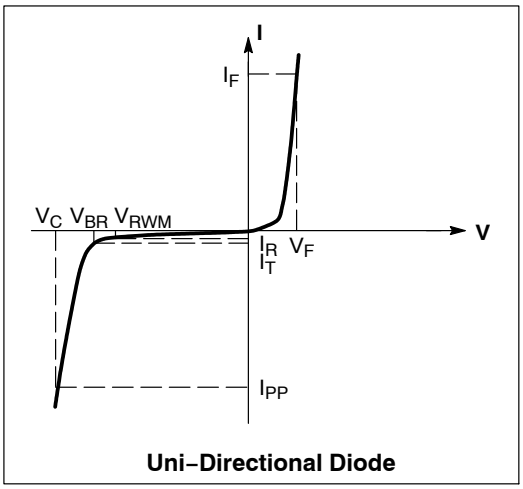
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ T_L = 25°C, t_P = 100 μs	P_{ZSM}	600	W
DC Power Dissipation @ T_L = 75°C Measured Zero Lead Length (Note 2) Derate Above 75°C Thermal Resistance, Junction−to−Lead	P_D $R_{\theta JL}$	1.5 20 50	W mW/°C °C/W
Forward Surge Current (Note 3) @ T_A = 25°C	I_{FSM}	40	A
Operating and Storage Temperature Range	T_J, T_{stg}	−65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. 100 μs, non−repetitive square pulse
2. 1 in. square copper pad, FR−4 board
3. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum



Uni−Directional Diode

SYMBOLS DEFINITIONS

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, V_F = 1.2 V Max. @ I_F = 0.5 A for all types)

Device*	Device Marking	V_{RWM} (Note 4)	I_R @ V_{RWM}	Breakdown Voltage				Z_{zt} @ I_T	
				V_{BR} (V) (Note 5)			@ I_T	Typ	Max
		Volts	μA	Min	Nom	Max	mA	Ω	Ω
BZG03C15, G	G15	11	1	13.8	15.0	15.6	50	5.0	10.0
BZG03C150, G	G150	110	1	138	150	156	5	130	300

4. A transient suppressor is normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level
5. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C

*The “G” suffix indicates Pb−Free package available.

RATING AND TYPICAL CHARACTERISTIC CURVES

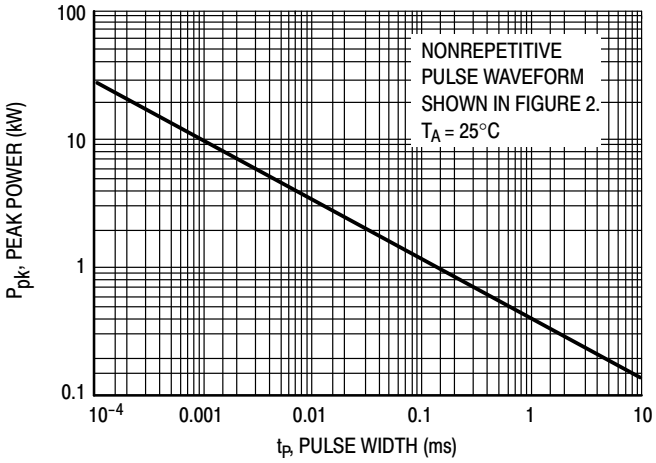


Figure 1. Pulse Rating Curve

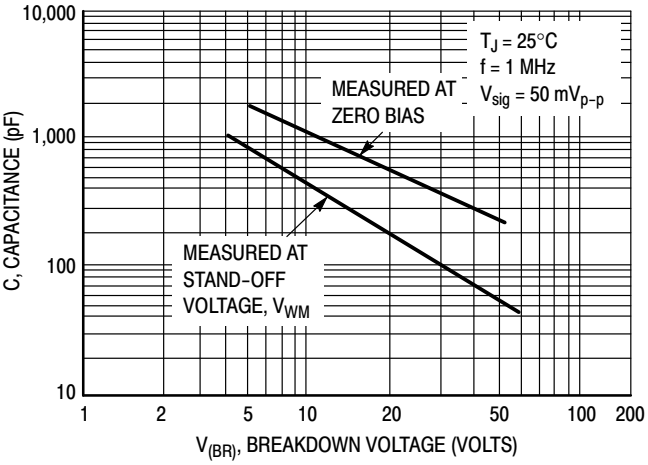


Figure 3. Typical Junction Capacitance

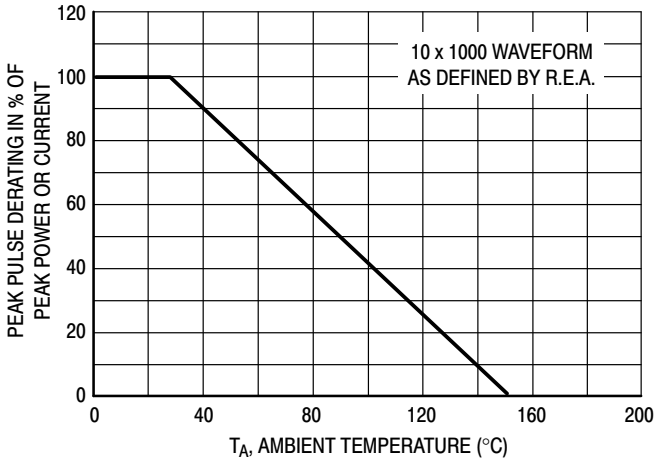


Figure 2. Pulse Derating Curve

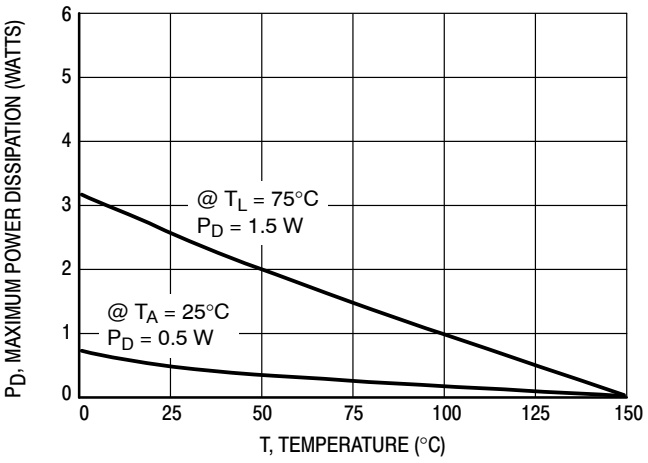


Figure 4. Steady State Power Derating

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

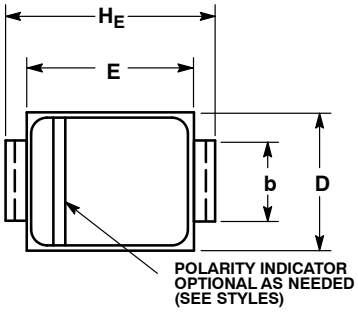
ON Semiconductor®

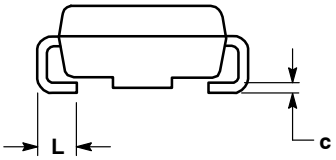
SMA
CASE 403D
ISSUE H

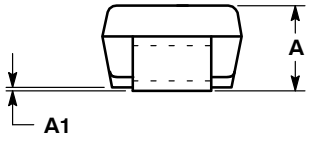
DATE 23 SEP 2015

STYLE 1 STYLE 2

SCALE 1:1



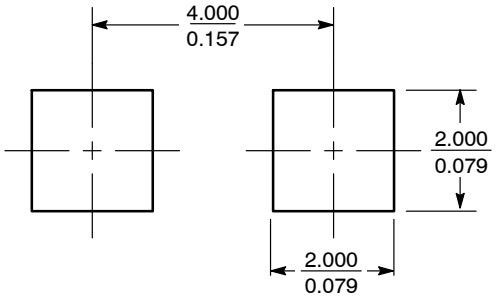




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION b SHALL BE MEASURED WITHIN DIMENSION L.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.97	2.10	2.20	0.078	0.083	0.087
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.27	1.45	1.63	0.050	0.057	0.064
c	0.15	0.28	0.41	0.006	0.011	0.016
D	2.29	2.60	2.92	0.090	0.103	0.115
E	4.06	4.32	4.57	0.160	0.170	0.180
H_E	4.83	5.21	5.59	0.190	0.205	0.220
L	0.76	1.14	1.52	0.030	0.045	0.060

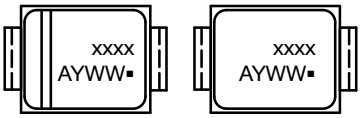
SOLDERING FOOTPRINT*



SCALE 8:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



STYLE 1 STYLE 2

xxxx = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1:
PIN 1. CATHODE (POLARITY BAND)
2. ANODE

STYLE 2:
NO POLARITY

DOCUMENT NUMBER:	98AON04079D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	SMA		PAGE 1 OF 1

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊